TOSHIBA 2SC2670

## TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

## 2 S C 2 6 7 0

HIGH FREQUENCY AMPLIFIER APPLICATIONS AM HIGH FREQUENCY AMPLIFIER APPLICATIONS AM FREQUENCY CONVERTER APPLICATIONS

Low Noise Figure : NF = 3.5dB (Max.) (f = 1 MHz)

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{\mathrm{CBO}}$	35	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{ m EBO}$	4	V
Collector Current	IC	100	mA
Base Current	$I_{\mathbf{B}}$	20	mA
Collector Power Dissipation	PC	200	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

4.2MAX 0.55MAX **EMITTER COLLECTOR** BASE **JEDEC EIAJ TOSHIBA** 2-4E1A

Unit in mm

Weight: 0.13 g

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 35 \text{ V}, I_{E} = 0$	_	_	0.1	$\mu$ A
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 4 \text{ V}, I_{C} = 0$	_	_	1.0	$\mu$ A
DC Current Gain	hFE (Note)	$ m V_{CE} = 12  V,  I_{C} = 2  mA$	40	_	240	_
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	$I_{\mathrm{C}} = 10 \mathrm{mA}, \; I_{\mathrm{B}} = 1 \mathrm{mA}$	_	_	0.4	V
Base-Emitter Saturation Voltage	V <sub>BE</sub> (sat)	$I_{\mathrm{C}} = 10 \mathrm{mA}, \; I_{\mathrm{B}} = 1 \mathrm{mA}$	_	_	1.0	V
Transition Frequency	$ m f_{T}$	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	80	_	_	MHz
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	$ m V_{CE} = 10 \ V, \ f = 1 \ MHz$	_	2.2	3.0	pF
Collector-Base Time Constant	C <sub>c</sub> .r <sub>bb</sub> ,	$V_{CE} = 10 \text{ V}, I_{E} = -1 \text{ mA},$ f = 30  MHz	_	_	50	ps
Noise Figure	NF	$V_{ ext{CE}} = 10 \text{ V}, \ I_{ ext{E}} = -1 \text{ mA}, \ f = 1 \text{ MHz}, \ R_{ ext{g}} = 50 \ \Omega$	_	2.0	3.5	dB

(Note): hFE Classification  $R: 40\sim80, O: 70\sim140, Y: 120\sim240$ 

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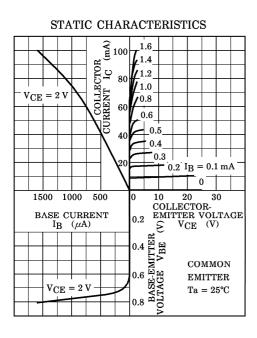
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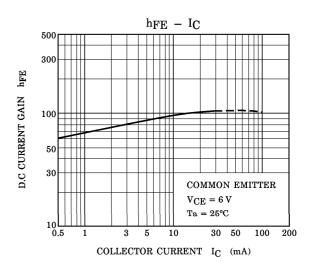
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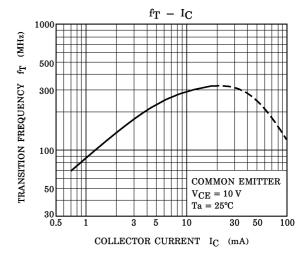
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Y PARAMETERS (Typ.) (COMMON EMITTER	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 1 \text{ MHz}$
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CHARACTERISTIC	SYMBOL	2SC2670-R	2SC2670-O	2SC2670-Y	UNIT
Input Conductance	gie	0.5	0.35	0.22	mS
Input Capacitance	$c_{ie}$	50	48	46	pF
Output Conductance	goe	4	5	6.5	μS
Output Capacitance	Coe	3.7	3.4	3.2	pF
Forward Transfer Admittance	lуfel	36	36	36	mS
Phase Angle of Forward Transfer Admittance	$\theta_{\mathbf{fe}}$	-1.6	-1.6	-1.6	0
Reverse Transfer Admittance	y <sub>re</sub>	14	14	14	μS
Phase Angle of Reverse Transfer Admittance	$\theta_{ extbf{re}}$	-90	-90	-90	0







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